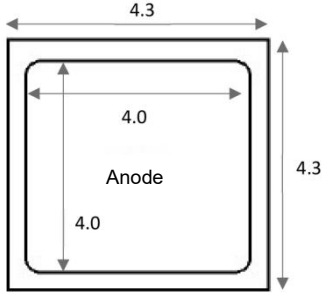


Physical Characteristics

	Die size: 4.3 mm x 4.3 mm (without scribe line) Anode pad open size: 4.0 mm x 4.0 mm Gross die / per 6" wafer = 784pcs
	Main characteristics: $V_{RRM} = 1700V$ $I_F = 25A$ $Q_C = 200nC$

Mechanical Data

Parameter	Parameter
Nominal Back Metal Composition, Thickness	Ti- Ni - Ag(1.4μm)
Nominal Front Metal Composition, Thickness	Al(4.2μm)
Wafer Diameter	150mm
Wafer Thickness	175μm
Scribe line width	100μm
Passivation	Polyimide

Absolute Maximum Ratings($T_C=25^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Test Condition	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		1700	V
Continuous Forward Current	I_F		25	A
Non-Repetitive Forward Surge Current	I_{FSM}	$t_P = 10ms$	100	A
Repetitive Forward Surge Current	I_{FRM}	$t_P = 10ms$	75	A

Note: These are stress ratings only and functional operation is not implied. Exposure to absolute maximum ratings for prolonged time periods may affect device reliability.

Electrical Specifications($T_C=25^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Reverse Blocking Voltage	V_R	$I_R = 250\mu A$	1700			V
Reverse Current	I_R	$V_R = 1700V, T_J = 25^{\circ}C$		5	100	μA
		$V_R = 1700V, T_J = 175^{\circ}C$		60	200	
Forward Voltage	V_F	$I_F = 25A, T_J = 25^{\circ}C$		1.6	1.9	V
		$I_F = 25A, T_J = 175^{\circ}C$		2.5	2.9	

Note: All characteristics are tested with the parts assembled in TO-247-2 package.